

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A substrate processing apparatus for removing an organic matter from a substrate by a remover for said organic matter, comprising:

a holding-and-rotating section for holding and rotating a substrate;

a remover supplying section for supplying a remover for removing an organic matter to the substrate held by said ~~holding~~ holding-and-rotating section; and

a gas supplying section for supplying an inert gas ~~to the substrate held by said holding and rotation section~~ to a surface of the substrate substantially concurrently with a supply of said remover to said substrate.

2. (Original) The substrate processing apparatus according to claim 1, wherein said remover supplying section has a remover supplying tube for discharging a remover to a substrate, and

said gas supplying section has a gas supplying tube for blowing an inert gas on said substrate.

3. (Original) The substrate processing apparatus according to claim 2, wherein said remover supplying tube is set in said gas supplying tube.

4. (Currently Amended) The substrate processing apparatus according to ~~claims~~ claim 3, further comprising:

an exhausting section set to a side of the substrate held by said ~~holding~~ holding-and-rotating section to exhaust a gas nearby said substrate.

5. (Cancelled)

6. (Currently Amended) The substrate processing apparatus according to claim 4 [5], wherein said organic matter attached to said substrate is a reaction product produced when a resist film formed on said substrate changes in quality.

7. (Original) The substrate processing apparatus according to claim 6, wherein said reaction product is a polymer produced when a thin film present on the surface of said substrate is dry-etched by using said resist film as a mask.

8. (Original) The substrate processing apparatus according to claim 1, wherein said gas supplying section is provided with a gas nozzle having a slit-like gas-blowing port for blowing an inert gas along the surface of the substrate held by said holding-and-rotating section and said gas nozzle is set to a side of the substrate held by said holding-and-rotating section.

9. (Original) The substrate processing apparatus according to claim 8, further comprising:

an aspirating section for aspirating a gas nearby the substrate held by said holding-and-rotating section, said aspirating section being located opposite said gas nozzle with said substrate sandwiched in between.

10. (Original) The substrate processing apparatus according to claim 9, wherein
said remover supplying section starts supplying a remover to a substrate and when a
predetermined time elapses, said gas supplying section starts supplying an inert gas to said
substrate.

11. (Original) The substrate processing apparatus according to claim 10, wherein
said organic matter attached to said substrate is a reaction product produced when a resist
film formed on said substrate changes in quality.

12. (Original) The substrate processing apparatus according to claim 11, wherein
said reaction product is a polymer produced when a thin film present on the surface of
said substrate is dry-etched by using said resist film as a mask.

13. (Currently Amended) A substrate processing method for removing an organic matter
from a substrate by a remover for said organic matter, comprising the steps of:

holding and rotating a substrate;

supplying a remover for removing an organic matter to said rotating substrate;

and

supplying an inert gas ~~to said rotating substrate~~ to a surface of the substrate substantially
concurrently with said supplying of a remover.

14. (Original) The substrate processing apparatus according to claim 13, wherein it is started to supply a remover to said substrate and when a predetermined time elapses, it is started to supply an inert gas to said substrate.

15. (Original) The substrate processing apparatus according to claim 14, wherein said organic matter attached to said substrate is a reaction product produced when a resist film formed on said substrate changes in quality.

16. (Original) The substrate processing apparatus according to claim 15, wherein said reaction product is a polymer produced when a thin film present on the surface of said substrate is dry-etched by using said resist film as a mask.

17. (New) The substrate processing apparatus according to claim 1, further comprising:

a controller for controlling said remover supplying section and said gas supplying section in such a manner that a supply period of said remover and a supply period of said inert gas to the substrate at least in part overlap.

18. (New) The substrate processing apparatus according to claim 17, wherein said controller controls said remover supplying section and said gas supplying section in such a manner that said remover supplying section starts supplying a remover to a substrate and, when a predetermined time elapses, said gas supplying section starts supplying an inert gas to said substrate.

19. (New) The substrate processing apparatus according to claim 13, wherein
a supply period of said remover and a supply period of said inert gas to the substrate at
least in part overlap.